TOSHIBA Variable Capacitance Diode Silicon Epitaxial Planar Type

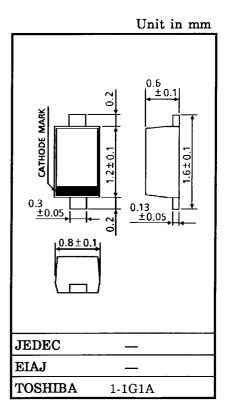
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Useful for VCO/TCXO

- Small Package
- High Capacitance Ratio: $C_{1V}/C_{4V} = 3.75$ (typ.)
- Low Series Resistance $: r_s = 0.45 \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V _R	10	V
Junction temperature	Тј	125	°C
Storage temperature range	T _{stg}	-55~125	°C



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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse voltage	VR	$I_R = 1 \ \mu A$	10	—	—	V
Reverse current	I _R	V _R = 10 V	_	_	3	nA
Capacitance	C _{1V}	$V_R = 1 V$, f = 1 MHz	17	18	19	рF
	C _{4V}	$V_R = 4 V$, f = 1 MHz	4.25	4.8	5.43	
Capacitance ratio	C _{1V} /C _{4V}	—	3.5	3.75	_	
Series resistance	r _s	$V_{R} = 1 V, f = 470 MHz$	_	0.45	0.7	Ω

Marking



